January 2001

Si9435DY

SEMICONDUCTOR IM

P-Channel Logic Level PowerTrench[®] MOSFET

General Description

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

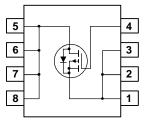
Applications

- DC/DC converter
- Load switch
- Motor Drive



Features

- -5.3 A, -30 V. $R_{DS(ON)} = 50 \text{ m}\Omega @ V_{GS} = -10 \text{ V}$ $R_{DS(ON)} = 80 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$
- Low gate charge
- Fast switching speed
- High performance trench technology for extremely low R_{DS(ON)}
- High power and current handling capability



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol		Parameter	Ratings	Units	
V _{DSS}	Drain-Source	Voltage	-30		
V _{GSS}	Gate-Source	√oltage	±20	V	
I _D	Drain Current	 Continuous 	(Note 1a)	-5.3	А
		– Pulsed		-20	
P _D	Power Dissipa	ation for Single Oper	ration (Note 1a)	2.5	W
			(Note 1b)	1.2	
			(Note 1c)	1.0	
T _J , T _{STG}	Operating and	I Storage Junction T	-55 to +150	°C	
Therma	I Characte	eristics			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)			50	°C/W
R _{eJC}	Thermal Resistance, Junction-to-Case (Note 1)		25	°C/W	
Packag	e Marking	and Orderin	g Information		
Device Marking		Device	Reel Size	Tape width	Quantity
9435		Si9435DY	13"	12mm	2500 units

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Si9435DY

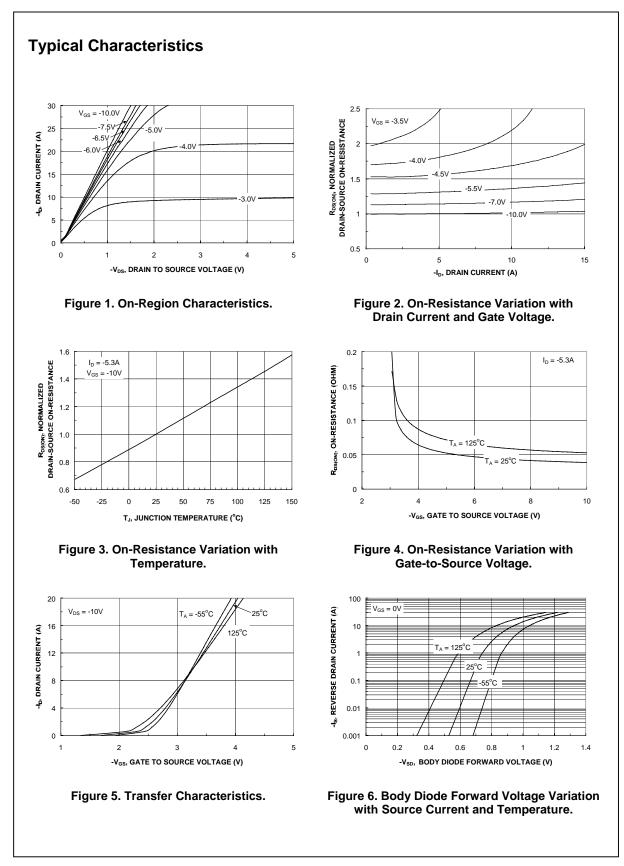
acteristics Drain–Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ $I_D = -250 \mu\text{A}, \text{ Referenced to } 25^\circ\text{C}$	-30			V
Drain–Source Breakdown Voltage Breakdown Voltage Temperature Coefficient		-30			V
Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C				
Zero Gate Voltage Drain Current			-22		mV/∘C
Zero Gute Voltage Drain Guttern	$V_{DS} = -24 V$, $V_{GS} = 0 V$			-1	μA
Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
	•				
···· · · · · · · · · · · · · · · · · ·	$V_{DS} = V_{CS}$, $I_D = -250 \text{ µA}$	-1	-1.7	-3	V
Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		4		mV/°C
Static Drain–Source On–Resistance	$ \begin{array}{ll} V_{GS} = -10 \ V, & I_D = -5.3 \ A \\ V_{GS} = -10 \ V, \ I_D = -5.3 \ A, \ T_J = 125^\circ C \\ V_{GS} = -4.5 \ V, \ I_D = -4.2A, \end{array} $		38 54 55	50 79 80	mΩ
On–State Drain Current	$V_{GS} = -10 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-20			А
Forward Transconductance	$V_{DS} = -15 \text{ V}, \qquad I_D = -5.3 \text{ A}$		12		S
Characteristics					
	$V_{res} = -15 V$ $V_{res} = 0 V$		690		pF
	56 5 , 66 5 ,				pF
· ·			77		pF
			7	1/	ns
					ns
			-	-	ns
	•		-	-	ns
	$V_{} = 15 V_{} = 53 A_{}$			-	nC
	$V_{DS} = -15 V$, $I_D = -5.5 A$, $V_{GS} = -10 V$			25	nC
	•				nC
5					
Maximum Continuous Drain–Sourc		[-5.3	А
				-1.2	V
Drain–Source Diode Forward	$V_{GS} = 0 V$, $I_{S} = -5.3 A$ (Note 2)		-0.86		
	acteristics (Note 2) Gate Threshold Voltage Gate Threshold Voltage Temperature Coefficient Static Drain–Source On–Resistance On–State Drain Current Forward Transconductance Characteristics Input Capacitance Output Capacitance g Characteristics (Note 2) Turn–On Delay Time Turn–On Rise Time Turn–Off Fall Time Total Gate Charge Gate–Drain Charge Output Characteristics Output Capacitance g Characteristics (Note 2) Turn–On Rise Time Turn–Off Delay Time Turn–Off Fall Time Total Gate Charge Gate–Drain Charge Oate–Drain Charge	acteristics(Note 2)Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = -250 \ \mu$ AGate Threshold Voltage $I_D = -250 \ \mu$ A, Referenced to 25°CTemperature Coefficient $I_D = -250 \ \mu$ A, Referenced to 25°CStatic Drain–Source $V_{GS} = -10 \ V$, $I_D = -5.3 \ A$, $T_J=125°C$ On–Resistance $V_{GS} = -10 \ V$, $I_D = -4.2A$,On–State Drain Current $V_{GS} = -10 \ V$, $V_{DS} = -5 \ V$ Forward Transconductance $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$ Input Capacitance $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$ Input Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,Geharacteristics(Note 2)Turn–On Delay Time $V_{DD} = -15 \ V$, $I_D = -1 \ A$,Turn–Off Delay Time $V_{DS} = -10 \ V$, $R_{GEN} = 6 \ \Omega$ Turn–Off Fall Time $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$,Total Gate Charge $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$,Gate–Drain Charge $V_{DS} = -10 \ V$ Durce Diode Characteristics and Maximum Ratings	acteristics (Note 2)Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$ -1Gate Threshold Voltage $I_D = -250 \ \mu A$, Referenced to 25°C-1Gate Threshold Voltage $I_D = -250 \ \mu A$, Referenced to 25°C-20Static Drain–Source $V_{GS} = -10 \ V$, $I_D = -5.3 \ A$ -20On–Resistance $V_{GS} = -10 \ V$, $I_D = -4.2A$,-20On–State Drain Current $V_{GS} = -10 \ V$, $V_{DS} = -5 \ V$ -20Forward Transconductance $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$ -20Forward Transconductance $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$ -20Input Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,-20Generative Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,-20 Characteristics (Note 2)-20Turn–On Delay Time $V_{DD} = -15 \ V$, $I_D = -1 \ A$,-20Turn–On Rise Time $V_{DS} = -15 \ V$, $I_D = -1 \ A$,-20Turn–Off Delay Time $V_{DS} = -15 \ V$, $R_{GEN} = 6 \ \Omega$ -20Turn–Off Fall Time-10 \ V_{GS} = -10 \ V-20Gate–Drain Charge $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$,-20Gate–Drain Charge-10 \ V_{GS} = -10 \ V-20Druce Diode Characteristics and Maximum Ratings-20	acteristics (Note 2)Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = -250 \ \mu$ A, Referenced to 25°C4Gate Threshold Voltage Temperature Coefficient $I_D = -250 \ \mu$ A, Referenced to 25°C4Static Drain–Source $V_{GS} = -10 \ V$, $I_D = -5.3 \ A$, $V_{GS} = -10 \ V$, $I_D = -5.3 \ A$, $V_{GS} = -4.5 \ V$, $I_D = -4.2 \ A$,38On–Resistance $V_{GS} = -10 \ V$, $V_{DS} = -5 \ V$ -20Forward Transconductance $V_{GS} = -10 \ V$, $V_{DS} = -5 \ V$ -20Forward Transconductance $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$ 12CharacteristicsInput Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,690Output Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,690Output Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,10Turn–On Delay Time $V_{OD} = -15 \ V$, $I_D = -1 \ A$,7Turn–On Rise Time $V_{GS} = -10 \ V$, $R_{GEN} = 6 \ \Omega$ 10Turn–Off Delay Time $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$,14Gate–Source Charge $V_{OS} = -10 \ V$ 2.4Gate–Drain Charge $V_{OS} = -10 \ V$ 2.4Gate–Drain Charge $V_{AS} = -10 \ V$ 2.4Bate–Drain Charge $V_{AS} = -10 \ V$ 4.8	acteristics (Note 2)Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$ -1 -1.7 -3 Gate Threshold Voltage $I_D = -250 \ \mu A$, Referenced to 25° C4Static Drain–Source $V_{GS} = -10 \ V$, $I_D = -5.3 \ A$, $T_J = 125^{\circ}$ C3850On–Resistance $V_{GS} = -10 \ V$, $I_D = -5.3 \ A$, $T_J = 125^{\circ}$ C5479 $V_{GS} = -10 \ V$, $I_D = -4.2A$,5580On–State Drain Current $V_{GS} = -10 \ V$, $V_{DS} = -5 \ V$ -20Forward Transconductance $V_{DS} = -15 \ V$, $I_D = -5.3 \ A$ 12CharacteristicsNone690690Output Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,690Qutput Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,690Paracteristics $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,10Reverse Transfer Capacitance $V_{DS} = -15 \ V$, $V_{GS} = 0 \ V$,10 g Characteristics $V_{OS} = -10 \ V$, $R_{GEN} = 6 \ \Omega$ 10Turn–On Delay Time $V_{DS} = -10 \ V$, $R_{GEN} = 6 \ \Omega$ 10Turn–Off Delay Time $111 \ 20$ Total Gate Charge $V_{DS} = -15 \ V$, $V_{GS} = -10 \ V$ 2.4Gate–Source Charge $V_{OS} = -10 \ V$ 4.8Durce Diode Characteristics and Maximum Ratings

Scale 1 : 1 on letter size paper

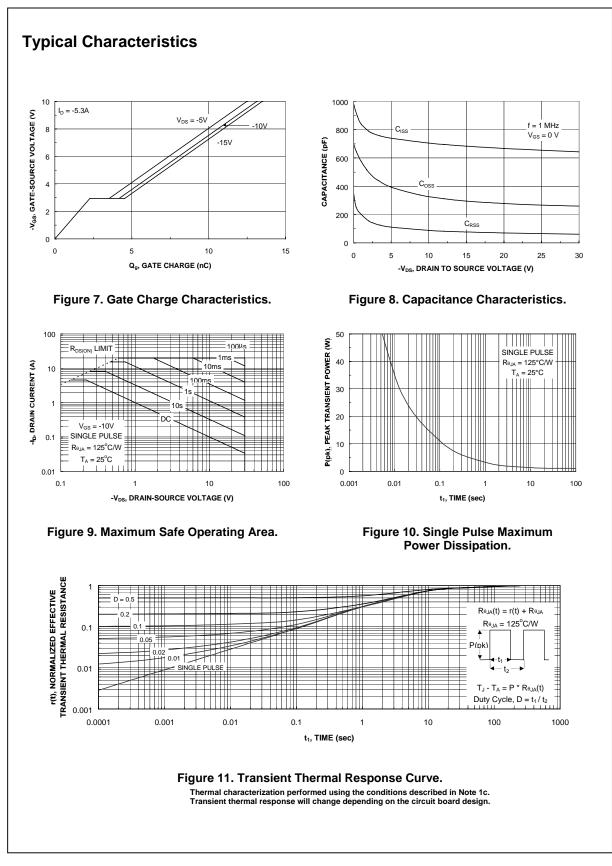
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2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

Si9435DY Rev A(W)

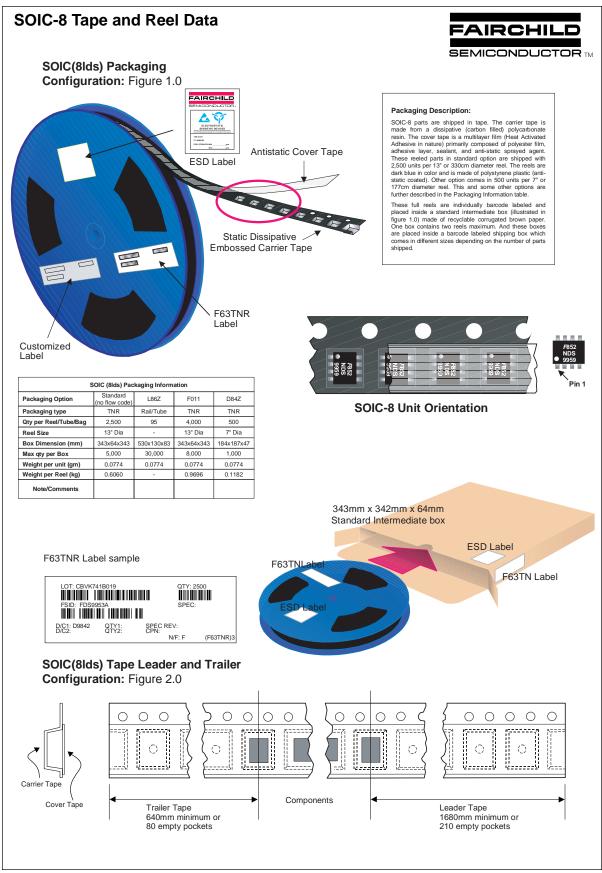


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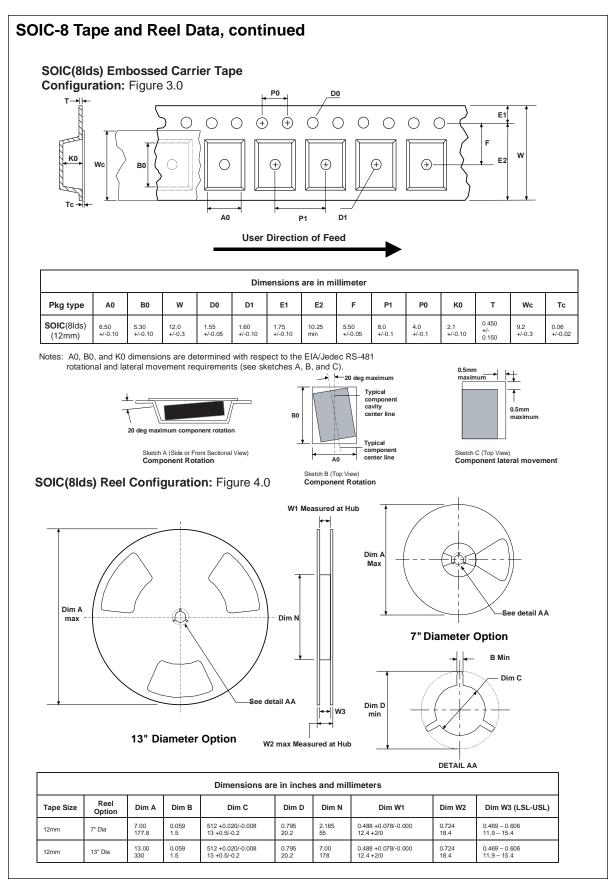
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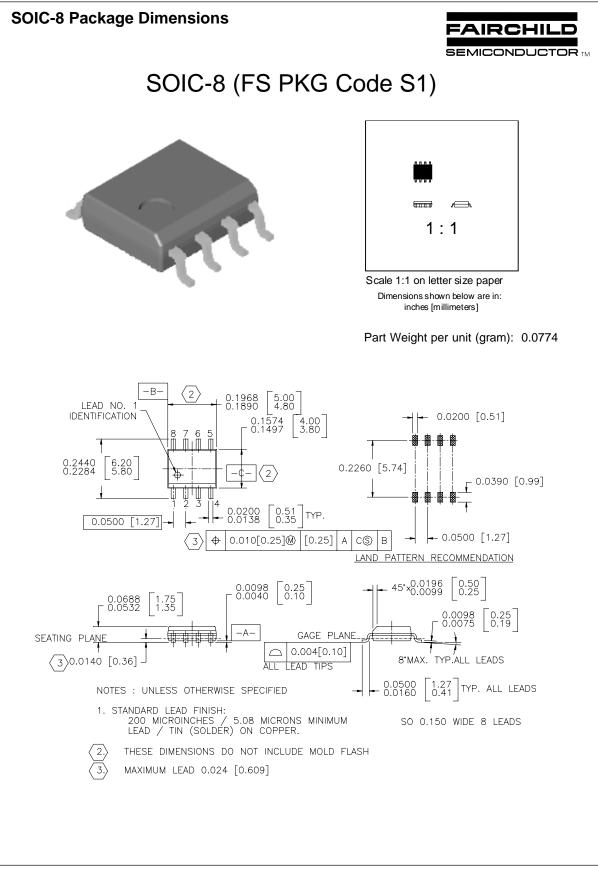
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